

2N5010

NPN Transistor

Package
 TO-5

Absolute Maximum Ratings	Symbol	Max	Unit
Power Dissipation	Power	4	W
Collector Current	I_C	0.5	A
Breakdown Voltage Collector-to-Base	$B_{V(CBO)}$	500	V
Voltage Collector to Emitter Open	V_{CEO}	500	V
Voltage Emitter to Base Open	BV_{EBO}	5	V

Electrical Characteristics	Symbol	Min	Typ	Max	Unit
Collector Emitter Saturation Voltage ($I_B=0.005$ mA, $I_C=0.025$ mA, $T_A=25$ °C, 300µs pulse)	$V_{CE(sat)}$			1.4	V
DC Current Gain ($I_C=0.025$ mA, $T_A=25$ °C, 300µs pulse)	HFE	30		180	

